

1200V SiC Schottky Diode

Amp+[™] Features

- Unipolar rectifier with surge current
- Zero reverse recovery current
- · Fast, temperature-independent switching
- Avalanche tested to 125mJ*
- All parts tested to greater than 1,400V

Amp+[™] Benefits

- Near zero switching loss
- Higher efficiency
- Smaller heat sink
- Easy to parallel

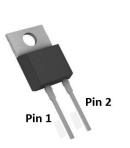
Amp+[™] Applications

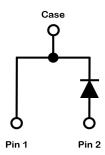
- Solar Inverters
- · Switch mode power supplies, UPS
- Power factor correction
- EV charging stations

GP3D010A120A

| VDC | 1200 V |
|---------------------|--------|
| Qc | 56 nC |
| I _F | 10 A |
| T _j ,max | 175 °C |







| Part # | Package | Marking |
|--------------|-----------|-----------|
| GP3D010A120A | TO-220-2L | 3D010A120 |



Maximum Ratings, at Ti=25 °C, unless otherwise specified

| Symbol | Conditions | Values | Unit | |
|---------------------------------------|--|--|--|--|
| I _{F**} | T _c =25 °C, T _j =175 °C | 33 | | |
| | T _C =125 °C, T _j =175 °C | 18 | A | |
| | T _C =150 °C, T _j =175 °C | 12 | | |
| 1 | T _C =25 °C, t _p =8.3 ms | 120 | • | |
| IFSM | T _C =110 °C, t _p =8.3 ms | 110 | — A | |
| I _{F,max} | T _C =25 °C, t _p =10 μs | 700 | A | |
| ∫i²dt | T _C =25 °C, t _p =8.3 ms | 60 | •2 | |
| | T _C =110 °C, t _p =8.3 ms | 50 | A ² s | |
| V _{RRM} | T _j =25 °C | 1200 | V | |
| dv/dt | Turn-on slew rate, repetitive | 200 | V/ns | |
| P _{tot**} | T _C =25 °C | 174 | W | |
| T _j , T _{storage} | Continuous | -55175 | °C | |
| T _{solder} | Wave soldering leads | 260 | °C | |
| | M3 Screw | 1 | N-m | |
| | I _{F**} I _{FSM} I _{F,max} $\int ji^2 dt$ V _{RRM} dv/dt P _{tot**} T _j , T _{storage} | $\label{eq:result} \begin{array}{ c c c c c } \hline T_{c}=25 \ ^{\circ}\text{C}, \ T_{j}=175 \ ^{\circ}\text{C} \\ \hline T_{c}=125 \ ^{\circ}\text{C}, \ T_{j}=175 \ ^{\circ}\text{C} \\ \hline T_{c}=150 \ ^{\circ}\text{C}, \ T_{j}=175 \ ^{\circ}\text{C} \\ \hline T_{c}=150 \ ^{\circ}\text{C}, \ T_{j}=175 \ ^{\circ}\text{C} \\ \hline T_{c}=110 \ ^{\circ}\text{C}, \ T_{p}=8.3 \ \text{ms} \\ \hline T_{c}=110 \ ^{\circ}\text{C}, \ t_{p}=8.3 \ \text{ms} \\ \hline T_{c}=25 \ ^{\circ}\text{C}, \ t_{p}=10 \ \mu\text{s} \\ \hline T_{c}=110 \ ^{\circ}\text{C}, \ t_{p}=8.3 \ \text{ms} \\ \hline T_{c}=110 \ ^{\circ}\text{C}, \ t_{p}=8.3 \ \text{ms} \\ \hline T_{c}=110 \ ^{\circ}\text{C}, \ t_{p}=8.3 \ \text{ms} \\ \hline T_{c}=110 \ ^{\circ}\text{C}, \ t_{p}=8.3 \ \text{ms} \\ \hline \hline T_{c}=110 \ ^{\circ}\text{C}, \ t_{p}=8.3 \ \text{ms} \\ \hline \hline T_{c}=110 \ ^{\circ}\text{C}, \ t_{p}=8.3 \ \text{ms} \\ \hline \hline T_{c}=110 \ ^{\circ}\text{C}, \ t_{p}=8.3 \ \text{ms} \\ \hline \hline T_{c}=110 \ ^{\circ}\text{C}, \ t_{p}=8.3 \ \text{ms} \\ \hline \hline T_{c}=110 \ ^{\circ}\text{C}, \ t_{p}=8.3 \ \text{ms} \\ \hline \hline T_{c}=110 \ ^{\circ}\text{C}, \ t_{p}=8.3 \ \text{ms} \\ \hline \hline T_{c}=25 \ ^{\circ}\text{C} \\ \hline \hline T_{j}, \ T_{storage} \ \hline \hline Continuous \\ \hline \hline T_{solder} \ \hline Wave soldering leads \\ \hline \end{array}$ | $I_{F^{**}} = \begin{bmatrix} T_{C}=25 \ ^{\circ}C, \ T_{j}=175 \ ^{\circ}C & 33 \\ \hline T_{C}=125 \ ^{\circ}C, \ T_{j}=175 \ ^{\circ}C & 18 \\ \hline T_{C}=150 \ ^{\circ}C, \ T_{j}=175 \ ^{\circ}C & 12 \\ \hline T_{C}=150 \ ^{\circ}C, \ T_{j}=175 \ ^{\circ}C & 12 \\ \hline T_{C}=110 \ ^{\circ}C, \ T_{p}=8.3 \ ms & 120 \\ \hline T_{C}=110 \ ^{\circ}C, \ t_{p}=8.3 \ ms & 110 \\ \hline I_{F,max} & T_{C}=25 \ ^{\circ}C, \ t_{p}=10 \ \mu s & 700 \\ \hline f_{i}^{2}dt & \hline T_{C}=25 \ ^{\circ}C, \ t_{p}=8.3 \ ms & 60 \\ \hline T_{C}=110 \ ^{\circ}C, \ t_{p}=8.3 \ ms & 50 \\ \hline V_{RRM} & T_{j}=25 \ ^{\circ}C & 1200 \\ \hline dv/dt & \hline Turn-on \ slew \ rate, \ repetitive & 200 \\ \hline P_{tot^{**}} & T_{C}=25 \ ^{\circ}C & 174 \\ \hline T_{j}, \ T_{storage} & Continuous & -55175 \\ \hline T_{solder} & Wave \ soldering \ leads & 260 \\ \hline \end{bmatrix}$ | |

Notes:

* EAS of 125 mJ is based on starting Tj = 25°C, L = 1.0 mH, IAS = 15.81 A, V = 50 V.

** Typical Rth_{JC} used

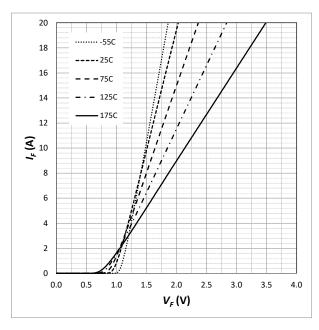
| Characteristics | Symbol | Conditions | Values | | | Unit |
|-------------------------|-----------------|--|--------|------|------|------|
| | Symbol | | min. | typ. | max. | Omt |
| DC blocking voltage | V _{DC} | T _j =25 °C | 1200 | - | - | V |
| Breakdown voltage | V _{BR} | I _R =1.00mA, T _j =25 °C | 1400 | - | - | V |
| Diode forward voltage | | I _F =10A, T _j =25 °C | - | 1.50 | 1.65 | v |
| | V _F | I _F =10A, T _j =125 °C | - | 1.83 | - | |
| | | I _F =10A, T _j =175 °C | - | 2.11 | 2.70 | |
| Reverse current | I _R | V _R =1,200V, T _j =25 °C | - | 2 | 20 | -μΑ |
| | | V _R =1,400V, T _j =25 °C | - | 7 | - | |
| | | V _R =1,200V, T _j =125 °C | - | 11 | - | |
| | | V _R =1,200V, T _j =175 °C | - | 39 | 300 | |
| Total capacitive charge | Q _C | V _R =800V, T _j =25 °C | - | 56 | - | nC |
| Total capacitance | | V _R =1V, f=1 MHz | - | 608 | - | pF |
| | С | V _R =400V, f=1 MHz | - | 53 | - | |
| | | V _R =800V, f=1 MHz | - | 39 | - | |

Electrical Characteristics, at T_j=25 °C, unless otherwise specified

Thermal Characteristics

| Characteristics | Symbol | Conditions | Values | | | Unit |
|-----------------------------------|------------|------------|--------|------|------|------|
| | | | min. | typ. | max. | Unit |
| Thermal resistance, junction-case | R_{thJC} | - | - | 0.86 | 1.11 | °C/W |

Typical Performance





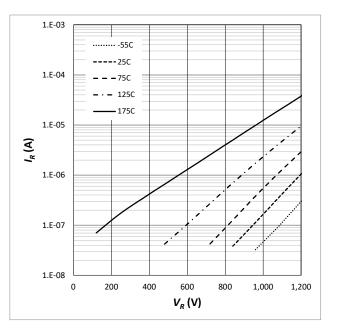


Fig. 2 Reverse Characteristics (parameterized on T_i)

200

180

160

140

120 **b**¹²⁰ **b**

80

60

40

20

0

25

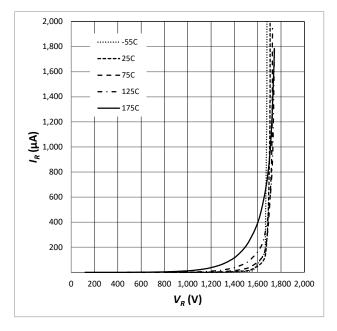




Fig. 4 Power Derating

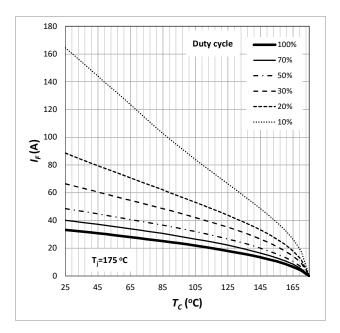
T_i=175 °C

75

125

т_с (°С)

175



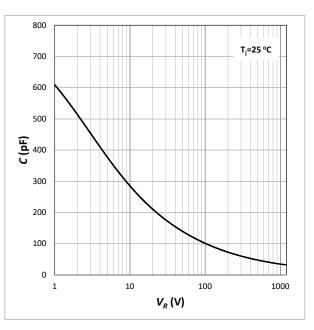
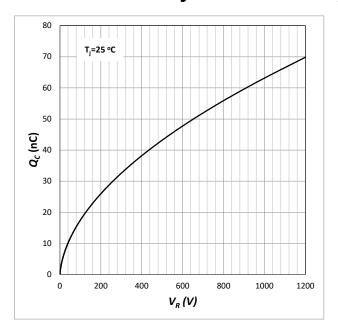


Fig. 5 Capacitance

Fig. 6 Capacitance

1200V SiC Schottky Diode



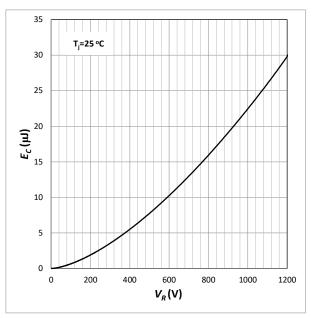


Fig. 7 Capacitive Charge

Fig. 8 Typical Capacitance Stored Energy

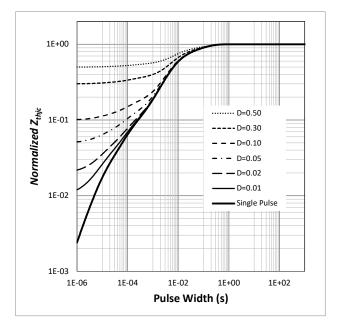


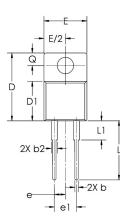
Fig. 9 Transient Thermal Impedance

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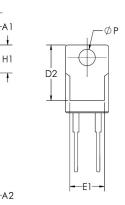
Amp +[™]

GP3D010A120A

Package Dimensions TO-220-2L



C



| - | Millin | neters | Inc | hes | |
|-----|----------|--------|-------|-------|--|
| Sym | Min | Max | Min | Max | |
| A | 3.56 | 4.83 | 0.140 | 0.190 | |
| A1 | 0.51 | 1.40 | 0.020 | 0.055 | |
| A2 | 2.03 | 2.92 | 0.080 | 0.115 | |
| b | 0.38 | 1.02 | 0.015 | 0.040 | |
| b2 | 1.02 | 1.78 | 0.040 | 0.070 | |
| с | 0.36 | 0.76 | 0.014 | 0.030 | |
| D | 14.22 | 16.51 | 0.560 | 0.650 | |
| D1 | 8.38 | 9.40 | 0.330 | 0.370 | |
| D2 | 12.19 | 13.13 | 0.480 | 0.517 | |
| E | 9.65 | 10.67 | 0.380 | 0.420 | |
| E1 | 6.86 | 8.89 | 0.270 | 0.350 | |
| е | 2.54 | BSC | .100 | BSC | |
| e1 | 5.08 BSC | | .200 | BSC | |
| H1 | 5.84 | 6.86 | 0.230 | 0.270 | |
| L | 12.57 | 14.73 | 0.495 | 0.580 | |
| L1 | 3.60 | 6.35 | 0.142 | 0.250 | |
| ØP | 3.53 | 4.09 | 0.139 | 0.161 | |
| Q | 2.54 | 3.43 | 0.100 | 0.135 | |

<u>Notes</u>

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.SemiQ.com.

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